AO6404

20V N-Channel MOSFET

General Description

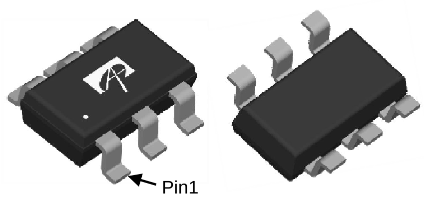
The AO6404 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected.

Product Summary

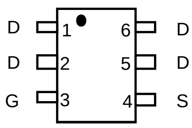
V_{DS} (V) = 20V
I_D = 8.6A (V_{GS} = 10V)
$R_{DS(ON)}$ < 17mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 18mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 24mΩ (V_{GS} = 2.5V)
$R_{DS(ON)}$ < 33mΩ (V_{GS} = 1.8V)
ESD Rating: 2000V HBM

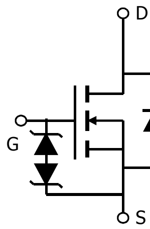
TSOP6

Top View   Bottom View



Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current [A]	T_A=25°C	I_D	8.6	A
	T_A=70°C		6.8	
Pulsed Drain Current [B]		I_{DM}	30	
Power Dissipation [A]	T_A=25°C	P_D	2	W
	T_A=70°C		1.28	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	45	62.5	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		70	110	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	33	50	°C/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V, V_{GS}=0V				10	µA
			T_J=55℃			25	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±10V				10	µA
BV_{GSO}	Gate-Source Breakdown Voltage	V_{DS}=0V, I_G=±250uA		±12			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		0.5	0.75	1	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V		30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=8.5A			13.4	17	mΩ
			T_J=125℃		16	20	
		V_{GS}=4.5V, I_D=5A			14.8	18	mΩ
		V_{GS}=2.5V, I_D=4A			18.8	24	mΩ
		V_{GS}=1.8V, I_D=3A			25.5	33	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=8A			36		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.73	1	V
I_S	Maximum Body-Diode Continuous Current					2.9	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz			1810		pF
C_{oss}	Output Capacitance				232		pF
C_{rss}	Reverse Transfer Capacitance				200		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			1.6		Ω
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=8.5A			17.9		nC
Q_{gs}	Gate Source Charge				1.5		nC
Q_{gd}	Gate Drain Charge				4.7		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=10V, R_L=1.2Ω, R_{GEN}=3Ω			2.5		ns
t_r	Turn-On Rise Time				7.2		ns
$t_{D(off)}$	Turn-Off DelayTime				49		ns
t_f	Turn-Off Fall Time				10.8		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=8.5A, dI/dt=100A/µs			22		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=8.5A, dI/dt=100A/µs			9.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 µs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev4: Feb. 2012

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

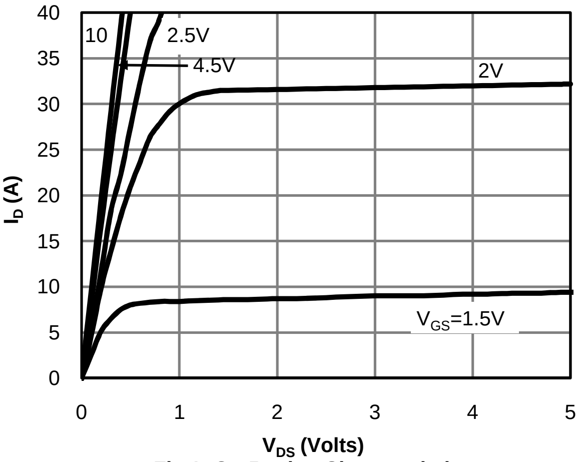


Fig 1: On-Region Characteristics

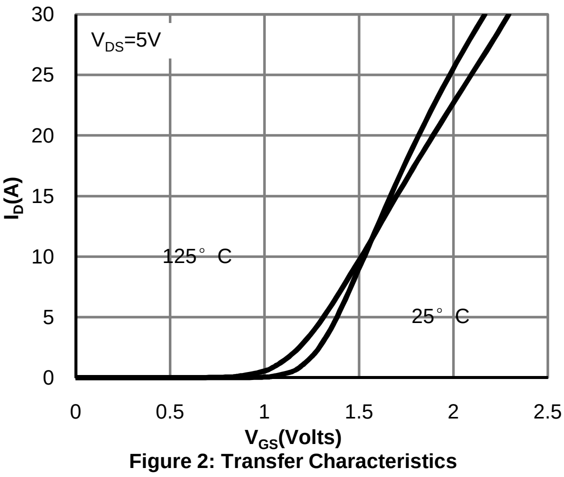


Figure 2: Transfer Characteristics

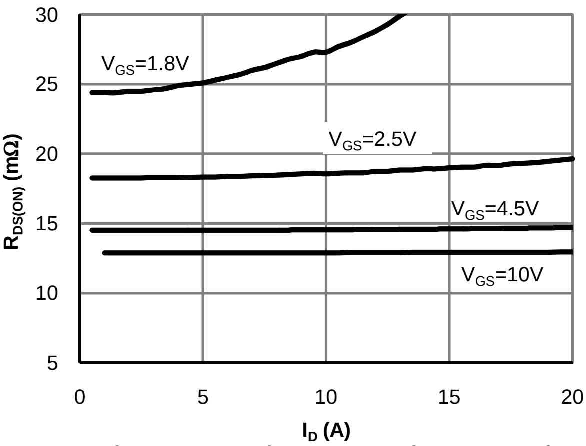


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

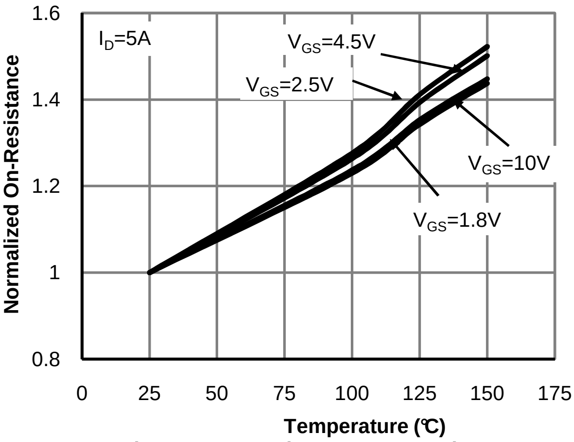


Figure 4: On-Resistance vs. Junction Temperature

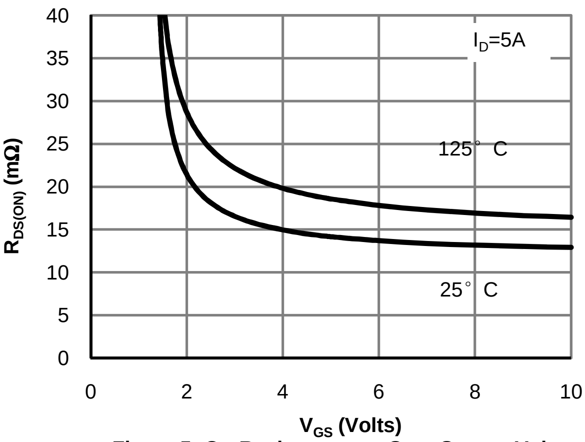


Figure 5: On-Resistance vs. Gate-Source Voltage

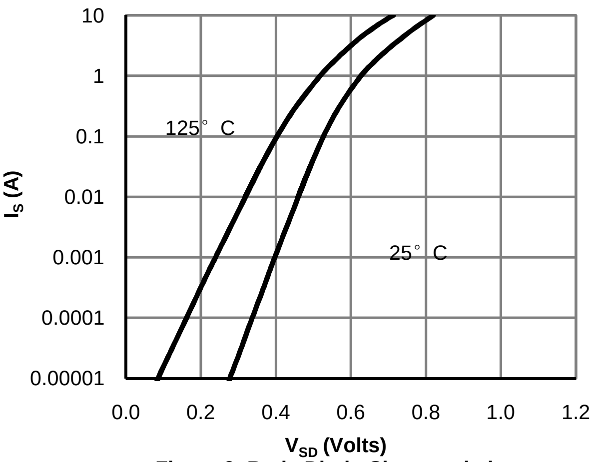


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

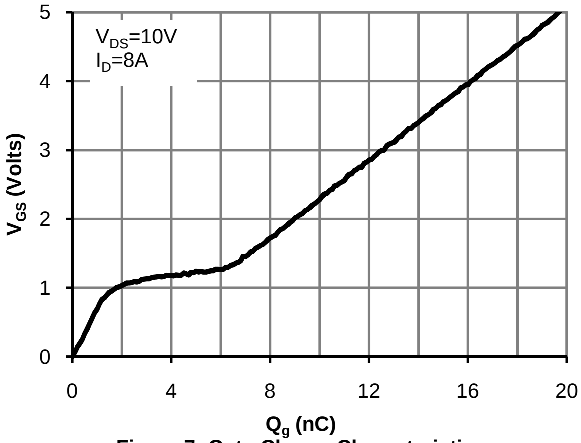


Figure 7: Gate-Charge Characteristics

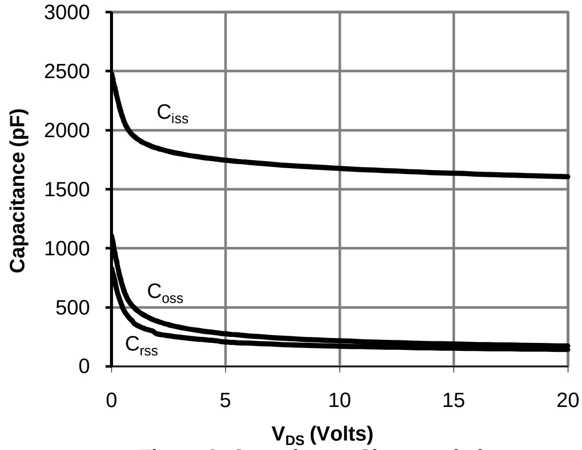


Figure 8: Capacitance Characteristics

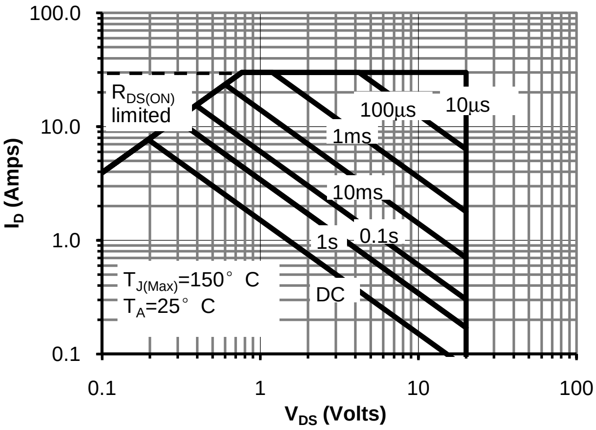


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

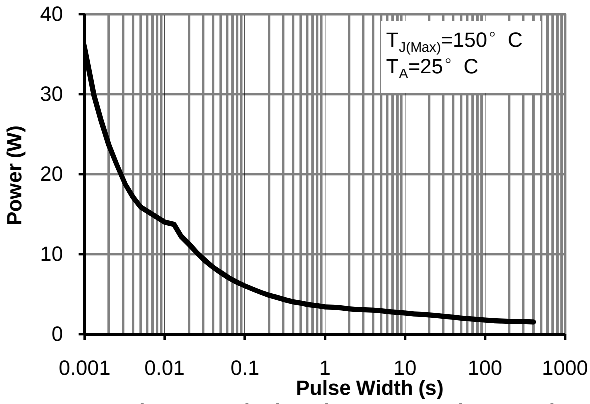


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

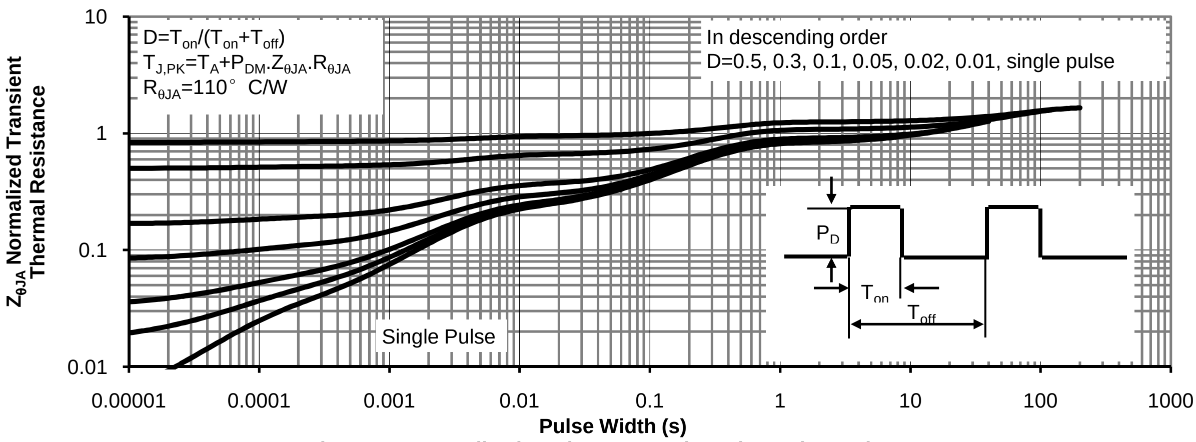


Figure 11: Normalized Maximum Transient Thermal Impedance